低温Al2O3/MoOx高性能工业级TOPCon太阳能电池

Lijuan Zhang[1], Hao Cheng[1], Jiawang Qiu[1], Zhongguo Zhou[1], Sihua Zhong[1], Linxing Shi[1], Haipeng Yin[2], Rui Tong[2], Jinghong Zhang[3], Xiaomin Song[1], and Zengguang Huang[1]

[1]Jiangsu Ocean University
[2]JA Solar
[3]Jinghaiyang Semiconductor Materials Co Ltd

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Abstract

Thanks to the excellent passivation, high conductivity, low parasitic absorption and simple process, the wide-bandgap doping-free carrier selective contacts have been attracting much attention. In this work, the wide-bandgap high work function of Al $_2$O $_3$/MoO $_x$ stacks were prepared using the low-temperature atomic layer deposition and thermal evaporation technique, respectively, and the interfacial evolution and the elements distribution were examined using high-resolution transmission electron microscopy coupled with energy-dispersive spectroscopy. The passivation and conductivity of the Al $_2$O $_3$/MoO $_x$ stacks were systematical investigated by varying their thicknesses. The high effective minority carriers lifetime of 513 μs and the low series resistance of 0.24 mΩ are realized on the 7nm-Al $_2$O $_3$/5nm-MoO $_x$ and 7nm-Al $_2$O $_3$/3nm-MoO $_x$ stacks, respectively. Benefiting from the excellent surface passivation and conductivity, the industrial size (182$\times$185.3 mm ^{2}) n-TOPCon solar cell with a total area front 7nm-Al $_2$O $_3$/3nm-MoO $_x$ stacks demonstrates a champion power conversion efficiency (PCE) of 24.48%, as well as a short-circuit current density of 41.06 mA cm $^{-2}$, an open-circuit voltage of 721 mV, and a fill factor of 82.66%. This work provides an effective way to enable the PCE over 26.0% and lower the process temperature for TOPCon solar cells with doping-free carrier selective contacts.